

CDMSJ22010-650

N-CHANNEL
SUPER JUNCTION MOSFET
10 AMP, 650 VOLT



TO-220FP CASE

Central
Semiconductor™

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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CDMSJ22010-650 is a high current, 650 Volt N-Channel power MOSFET designed for high voltage, fast switching applications such as Power Factor Correction (PFC), and power chargers. This MOSFET combines high voltage capability with low $r_{DS(ON)}$, low threshold voltage and low gate charge.

**MARKING: CDMSJ
10-650**

APPLICATIONS:

- Power Factor Correction
- TV Power
- UPS
- PD Charger
- Adapter

FEATURES:

- High voltage capability ($V_{DS}=650V$)
- Low gate charge ($Q_{GS}=4nC$)
- Low $r_{DS(ON)}$ (0.39Ω)

MAXIMUM RATINGS: ($T_C=25^\circ C$)

Drain-Source Voltage
Gate-Source Voltage
Continuous Drain Current
Continuous Drain Current ($T_C=100^\circ C$)
Pulsed Drain Current
Diode Forward Current
Power Dissipation
Power Dissipation ($T_C=100^\circ C$)
Operating and Storage Junction Temperature

SYMBOL

V_{DS}	650
V_{GS}	30
I_D	10
I_D	6.2
I_{DM}	22
I_S	10
P_D	29.5
P_D	12
T_J, T_{stg}	-55 to +150

UNITS

V
V
A
A
A
A
W
W
$^\circ C$

ELECTRICAL CHARACTERISTICS: ($T_J=25^\circ C$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	650	730		V
$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	3.0	4	V
$R_{DS(on)}$	$V_{GS}=10V, I_D=5.0A$ (Note 1)		340	390	m Ω
I_{DSS}	$V_{DS}=650V, V_{GS}=0V$			1.0	μA
I_{GSS}	$V_{GS}=30V, V_{DS}=0V$			100	nA
I_{GSSR}	$V_{GS}=30V, V_{DS}=0V$			100	nA
gfs	$V_{DS}=20V, I_D=11A$		10		S
Q_g	$V_{DS}=520V, I_D=11A, V_{GS}=10V$		19		nC
Q_{gs}	$V_{DS}=520V, I_D=11A, V_{GS}=10V$		4		nC

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ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Q_{gd}	$V_{DS}=520\text{V}$, $I_D=11\text{A}$, $V_{GS}=10\text{V}$		8		nC
C_{iss}	$V_{DS}=400\text{V}$, $V_{GS}=0\text{V}$, $f=250\text{kHz}$		726		pF
C_{oss}	$V_{DS}=400\text{V}$, $V_{GS}=0\text{V}$, $f=250\text{kHz}$		29		pF
C_{rss}	$V_{DS}=400\text{V}$, $V_{GS}=0\text{V}$, $f=250\text{kHz}$		8		pF
$C_{o(er)}$	$V_{DS}=0\text{V}$ to 400V , $V_{GS}=0\text{V}$, $f=250\text{kHz}$		37		pF
$t_{d(on)}$	$V_{DD}=325\text{V}$, $I_D=11\text{A}$, $V_{GS}=10\text{V}$, $R_G=25\Omega$		30		ns
t_r	$V_{DD}=325\text{V}$, $I_D=11\text{A}$, $V_{GS}=10\text{V}$, $R_G=25\Omega$		50		ns
$t_{d(off)}$	$V_{DD}=325\text{V}$, $I_D=11\text{A}$, $V_{GS}=10\text{V}$, $R_G=25\Omega$		87		ns
t_f	$V_{DD}=325\text{V}$, $I_D=11\text{A}$, $V_{GS}=10\text{V}$, $R_G=25\Omega$		42		ns
R_g	$f=1.0\text{MHz}$		6.8		Ω
V_{SD}	$I_S=10\text{A}$, $V_{GS}=0\text{V}$		0.89	1.5	V
Q_{rr}	$I_S=11\text{A}$, $di/dt=100\text{A}/\mu\text{s}$		3.3		μC
t_{rr}	$I_S=11\text{A}$, $di/dt=100\text{A}/\mu\text{s}$		291		ns

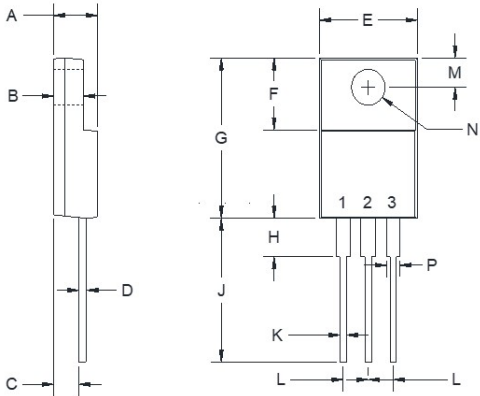
Note 1: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

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TO-220FP CASE - MECHANICAL OUTLINE



R5

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.165	0.202	4.20	5.12
B	0.090	0.130	2.30	3.30
C	0.098	0.122	2.50	3.10
D	-	0.031	-	0.80
E	0.382	0.418	9.70	10.63
F	0.238	0.276	6.06	7.00
G	0.583	0.640	14.80	16.25
H	-	0.177	-	4.50
J	0.503	0.543	12.78	13.80
K	0.020	0.035	0.50	0.90
L	0.100		2.54	
M	0.100	0.140	2.55	3.55
N (DIA)	0.116	0.134	2.95	3.40
P	0.039	0.058	1.00	1.47

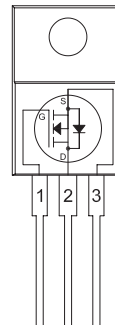
TO-220FP (REV: R5)

LEAD CODE:

- 1) Gate
- 2) Drain
- 3) Source

**MARKING CODE: CDMSJ
10-650**

PIN CONFIGURATION



R2 (30-October 2023)

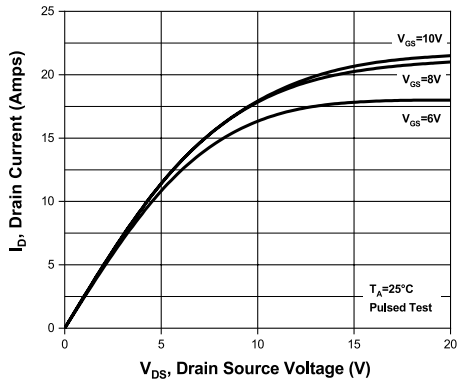
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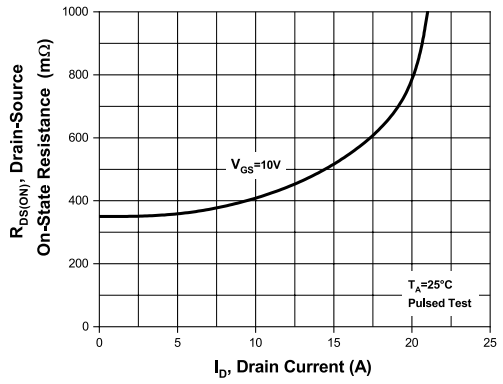


TYPICAL ELECTRICAL CHARACTERISTICS

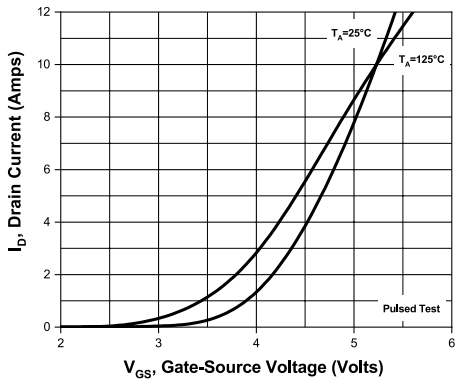
Typical Output Characteristics



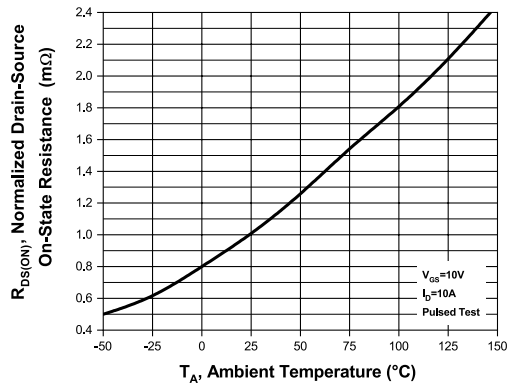
Drain Source On Resistance



Transfer Characteristics



Drain Source Temperature Coefficient



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TYPICAL ELECTRICAL CHARACTERISTICS

